

10 AMP, 75V, 3 PHASE MOSFET BRIDGE WITH INTELLIGENT INTEGRATED GATE DRIVE

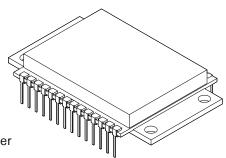
4400

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FEATURES:

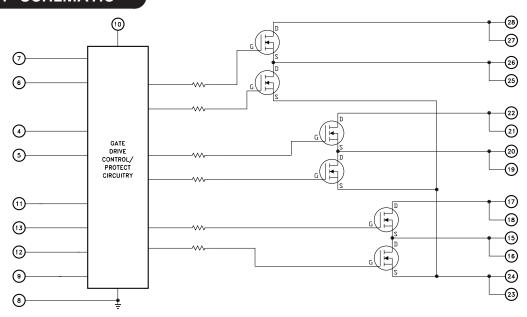
- 75 Volt Motor Supply Voltage
- · 10 Amp Output Switch Capability, All N-Channel MOSFET Output Bridge
- 100% Duty Cycle High Side Conduction Capable
- · Suitable for PWM Applications from DC to 100KHz
- · Shoot-Through/Cross Conduction Protection
- · Undervoltage Lockout Protection
- · Programmable Dead-Time Control
- · Low Active Enable for Bridge Shutdown Control
- · Isolated Base Plate Design for High Voltage Isolation Plus Good Thermal Transfer



DESCRIPTION:

The MSK 4400 is a 3 phase MOSFET bridge plus drivers in a convenient isolated baseplate package. The module is capable of 10 amps of output current and 75 volts of DC bus voltage. It has a full line of protection features, including undervoltage lockout protection of the bias voltage, cross conduction control and a user programmable dead-time control for shoot-through elimination. In addition, the bridge may be shut down by using the ENABLE control. The MSK 4400 provides good thermal conductivity for the MOSFETs due to an isolated plate design that allows direct heat sinking of the device without insulators.

EQUIVALENT SCHEMATIC



TYPICAL APPLICATIONS

- 3 Phase Brushless DC Servo Control
 Fin Actuator Control
 Gimbal Control
- 3 Phase AC Induction Motor Control HVAC Blower Control

PIN-OUT INFORMATION

N/C	20	ВØ		
N/C	19	ВØ		
N/C	18	CV+	28	AV +
BH	17	CV+	27	AV +
BL	16	CØ	26	ΑØ
AL	15	CØ	25	AØ
\overline{AH}	14	N/C	24	RSENSE
GND	13	CH	23	RSENSE
SWR	12	CL	22	BV+
VBIAS	11	ĒN	21	BV+
	N/C N/C BH BL AL AH GND SWR	N/C 19 N/C 18 BH 17 BL 16 AL 15 AH 14 GND 13 SWR 12	N/C 19 BØ N/C 18 CV + BH 17 CV + BL 16 CØ AL 15 CØ AH 14 N/C GND 13 CH SWR 12 CL	N/C 19 BØ N/C 18 CV + 28 BH 17 CV + 27 BL 16 CØ 26 AL 15 CØ 25 AH 14 N/C 24 GND 13 CH 23 SWR 12 CL 22

ABSOLUTE MAXIMUM RATINGS

V+ High Voltage Supply3V transient to +75V	Өлс Thermal Resistance
V _{BIAS} Bias Supply	Tst Storage Temperature Range55°C to +150°C
VIND Logic Input Voltages0.3V to VBIAS +0.3V	TLD Lead Temperature Range
Iουτ Continuous Output Current	(10 Seconds Lead Only)+200°C
IPK Peak Output Current	Tc Case Operating Temperature40°C to +125°C
AØ, BØ, CØ	T _J Junction Temperature + 150°C
Rsense	

ELECTRICAL SPECIFICATIONS

Parameter	Test Condition		MSK 4400		
i arameter	@ 25°C unless otherwise specified	Min.	ı. Typ.③ Ma		units
CONTROL SECTION					
VBIAS Quiescent Current 4	All Inputs Off	-	6	7	mAmp
VBIAS Operating Current 4	f=20KHz, 50% Duty Cycle	-	22	25	mAmp
Undervoltage Threshold (Falling)		5.75	6.6	7.5	Volts
Undervoltage Threshold (Rising)		6.2	7.1	8.0	Volts
Low Level Input Voltage		-	-	0.8	Volts
High Level Input Voltage		2.7	-	-	Volts
Low Level Input Current	V _{IN} = 0V	60	100	135	μAmp
High Level Input Current	VIN = 5 V	-1	-	+ 1	μAmp
OUTPUT BRIDGE					
Drain-Source Breakdown Voltage	$ID = 100\mu A$, All Inputs Off	75	-	-	V
Drain-Source Leakage Current	Vps = 70V	-	-	50	μAmp
Drain-Source On Resistance (Each FET) 1	I _D = 25A	-	-	0.033	Ω
Voltage Drop Across Bridge Phase (2) (4)	I _D = 10A	-	1.3	1.5	VOLTS
SWITCHING CHARACTERISTICS					
Rise Time	V + = 38V	-	62	-	nSec
Fall Time	In=25A Peak	-	58	-	nSec
Enable Turn-On Prop Delay (Lower)		-	100	-	μSec
Enable Turn-Off Prop Delay (Lower)		-	100	-	μSec
Enable Turn-On Prop Delay (Upper)	SWR Resistor = ∞	-	2	-	μSec
Enable Turn-Off Prop Delay (Upper)	SWR Resistor = ∞	-	2	-	μSec
Dead Time	SWR = Open	6.0	7.0	8.0	μSec
Dead Time 4	<u>SWR</u> = 12K	0.3	0.5	0.7	μSec
SOURCE-DRAIN DIODE CHARACTERISTICS					
Forward Voltage	IsD = 10A	-	-	1.7	Volts
Reverse Recovery Time	IsD = 10A, $di/dt = 100A/\mu S$	-	120	-	nSec

NOTES:

- 1 Use for maximum MOSFET junction temperature calculations.
- (2) Use for overall efficiency and dissipation calculations.
- ③ Typical parameters are representative of actual device performance but are for reference only.
- (4) Parameter is 100% tested on production devices. All other parameters are guaranteed.
- (5) Continuous operation at or above absolute maximum ratings may adversely effect the device performance and/or life cycle.
- (6) When applying power to the device, apply the low voltage followed by the high voltage or alternatively, apply both at the same time. Do not apply high voltage without low voltage present.

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APPLICATION NOTES

MSK 4400 PINOUT DESCRIPTIONS

 $A\emptyset$, $B\emptyset$, $C\emptyset$ - Are the connections to the motor phase windings from the bridge output. The wiring to these pins should be sized according to the required current by the motor. There are no short circuit provisions for these outputs. Shorts to V+ or gound from these pins must be avoided or the bridge will be destroyed.

AL, BL, CL - Are the logic level inputs for controlling the low side switch for each of the three phases. A logic HIGH turns the low side output on, sinking the output current and pulling it down. If the corresponding high side switch is ON, the device will turn off the high side output, insert the dead time and then command the lowside output on. The low side input has priority over the high side input.

AH, BH, CH- Are the logic level inputs for controlling the high side switch for each of the three phases. A logic low turns the high side output ON, sourcing the output current and pulling it up. If the corresponding low side switch is ON, the device will ignore the high side input until the lowside is turned off and dead time has elapsed. Again, the lowside input has priority.

AV+,BV+,CV+- Are the power connections from the hybrid to the bus. The pins for each phase are brought out separately and must be connected together to the V+ source externally. The external wiring to these pins should be sized according to the RMS current required by the motor. These pins should be bypassed by a high quality monolithic ceramic capacitor for high frequencies and enough bulk capacitance for keeping the V+ supply from drooping. 1000μ F of bulk capacitance was used in the test circuit. The voltage range on these pins is from 16 volts up to 75 volts.

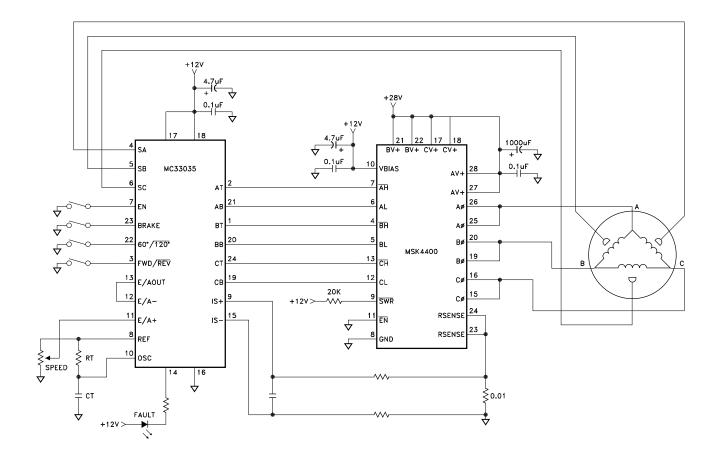
RSENSE - Is the connection point for the bottom of the three phase bridge. A low value resistor between here and the GND will produce a voltage proportional to current in the bridge. Both pins must be connected. If a resistor is not used, these pins must be connected to GND.

- **EN** Is the logic level input for enabling and disabling the bridge outputs. A logic low enables output switching.
- $\mbox{\bf GND}\,$ Is the logic input return connection, the VBIAS return and the V + return.
- **SWR** Is the control for the amount of dead time between a high side switch ON and the corresponding low side switch OFF and vice versa. Leaving it open creates the most dead time, while connecting a 12 K resistor to VBIAS creates the least.
- **VBIAS** Is the supply voltage for running all of the low level logic and gate drive functions. This pin should be bypassed to GND using a $0.1\mu F$ ceramic capacitor and a $4.7\mu F$ bulk capacitor.

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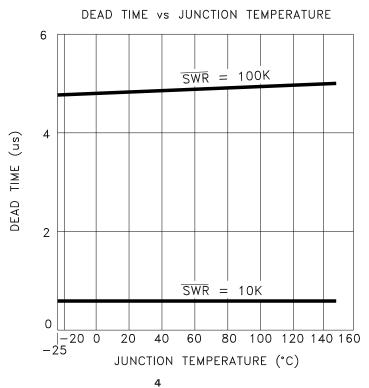
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TYPICAL APPLICATION SCHEMATIC

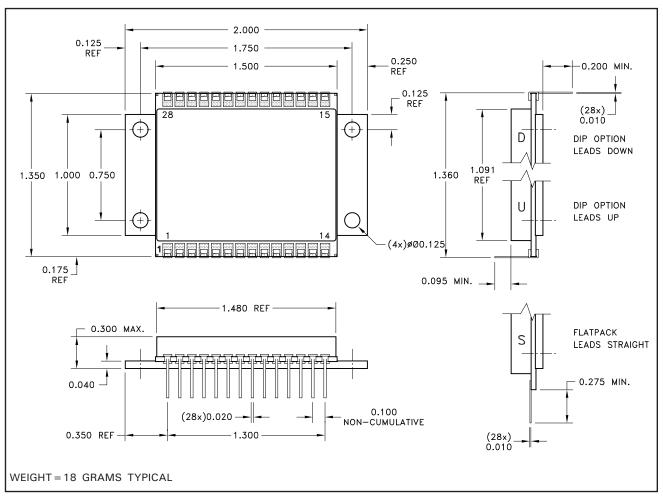


OPEN LOOP BRUSHLESS DC MOTOR SPEED CONTROL

TYPICAL PERFORMANCE CURVES



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NOTE: ALL DIMENSIONS ARE ±0.010 INCHES UNLESS OTHERWISE LABELED.

ORDERING INFORMATION

Part Number	Lead Option	Screening Level
MSK4400S	Straight	Industrial
MSK4400D	Down	Industrial
MSK4400U	Up	Industrial

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